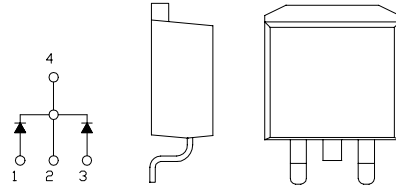


# SBD Type : C10T06Q

OUTLINE DRAWING

## FEATURES

- \*SQUARE-PAK TO-263AB(SMD)
- Packaged in 24mm Tape and Reel
- \*Dual Diodes – Cathode Common
- \*Low Forward Voltage Drop
- \*High Surge Capability
- \*T<sub>j</sub>=150 °C operation



## Maximum Ratings

Approx Net Weight: 1.4g

Rating	Symbol	C10T06Q			Unit
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	60			V
Non-repetitive Peak Reverse Voltage	V <sub>RSM</sub>	65			V
Average Rectified Output Current	I <sub>O</sub>	10	Tc=108°C	50 Hz Full Sine Wave Resistive Load	A
RMS Forward Current	I <sub>F(RMS)</sub>	11.1			A
Surge Forward Current	I <sub>FSM</sub>	110	50Hz Full Sine Wave ,1cycle Non-repetitive		A
Operating JunctionTemperature Range	T <sub>jw</sub>	-40 to +150			°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +150			°C

## Electrical • Thermal Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current	I <sub>RM</sub>	T <sub>j</sub> = 25°C, V <sub>RM</sub> = V <sub>RRM</sub> per arm	-	-	5	mA
Peak Forward Voltage	V <sub>FM</sub>	T <sub>j</sub> = 25°C, I <sub>FM</sub> = 5 A per arm	-	-	0.58	V
Thermal Resistance	R <sub>th(j-c)</sub>	Junction to Case	-	-	3	°C /W

# C10T06Q OUTLINE DRAWING (Dimensions in mm)

